



SLOVENSKI STANDARD
oSIST prEN IEC 63378-3:2024
01-junij-2024

Standardizacija toplotnih lastnosti pri polprevodniških ohišjih - 3. del: Simulacijski modeli toplotnih vezij diskretnih polprevodniških ohišij za prehodno analizo

Thermal standardization on semiconductor packages - Part 3: Thermal circuit simulation models of discrete semiconductor packages for transient analysis

Normalisation thermique des boîtiers de semiconducteurs - Partie 3: Modèles de simulation de circuits thermiques de boîtiers de semiconducteurs discrets pour analyse transitoire

Ta slovenski standard je istoveten z: prEN IEC 63378-3:2024

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ICS:

31.080.01	Polprevodniški elementi (naprave) na splošno	Semiconductor devices in general
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TITLE:

Thermal standardization on semiconductor packages - Part 3: Thermal circuit simulation models of discrete semiconductor packages for transient analysis

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

THERMAL STANDARDIZATION ON SEMICONDUCTOR PACKAGES –**Part 3: Thermal circuit simulation models of discrete semiconductor packages for transient analysis**

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Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

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